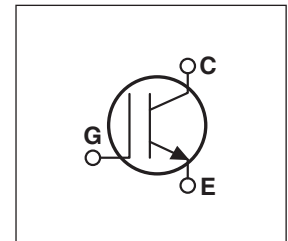
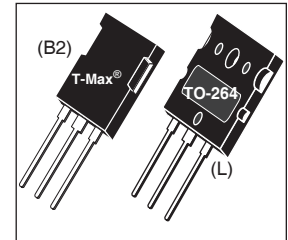


Utilizing the latest Field Stop and Trench Gate technologies, these IGBT's have ultra low $V_{CE(ON)}$ and are ideal for low frequency applications that require absolute minimum conduction loss. Easy paralleling is a result of very tight parameter distribution and a slightly positive $V_{CE(ON)}$ temperature coefficient. A built-in gate resistor ensures extremely reliable operation, even in the event of a short circuit fault. Low gate charge simplifies gate drive design and minimizes losses.

- **1200V Field Stop**
- **Trench Gate: Low $V_{CE(on)}$**
- **Easy Paralleling**
- **Intergrated Gate Resistor: Low EMI, High Reliability**



Applications: Welding, Inductive Heating, Solar Inverters, SMPS, Motor drives, UPS

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT75GN120B2_L(G)	UNIT
V_{CES}	Collector-Emitter Voltage	1200	Volts
V_{GE}	Gate-Emitter Voltage	± 30	
I_{C1}	Continuous Collector Current ^③ @ $T_C = 25^\circ\text{C}$	200	Amps
I_{C2}	Continuous Collector Current @ $T_C = 110^\circ\text{C}$	99	
I_{CM}	Pulsed Collector Current ^① @ $T_C = 150^\circ\text{C}$	225	
SSOA	Switching Safe Operating Area @ $T_J = 150^\circ\text{C}$	225A @ 1200V	
P_D	Total Power Dissipation	833	Watts
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 3mA$)	1200			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 3mA, T_J = 25^\circ\text{C}$)	5.0	5.8	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 75A, T_J = 25^\circ\text{C}$)	1.4	1.7	2.1	
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 75A, T_J = 125^\circ\text{C}$)		2.0		
I_{CES}	Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_J = 25^\circ\text{C}$) ^②			100	μA
	Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_J = 125^\circ\text{C}$) ^②			TBD	
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V$)			600	nA
$R_{G(int)}$	Intergrated Gate Resistor		10		Ω



CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

APT75GN120B2_L(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT	
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$		4800		pF	
C_{oes}	Output Capacitance			275			
C_{res}	Reverse Transfer Capacitance			210			
V_{GEP}	Gate-to-Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 600V$ $I_C = 75A$		9.0		V	
Q_g	Total Gate Charge ^③			425		nC	
Q_{ge}	Gate-Emitter Charge			30			
Q_{gc}	Gate-Collector ("Miller") Charge			245			
SSOA	Switching Safe Operating Area	$T_J = 150^\circ\text{C}, R_G = 4.3\Omega^{\text{⑦}}, V_{GE} = 15V, L = 100\mu\text{H}, V_{CE} = 1200V$	225			A	
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{CC} = 800V$ $V_{GE} = 15V$ $I_C = 75A$ $R_G = 1.0\Omega^{\text{⑦}}$ $T_J = +25^\circ\text{C}$		60		ns	
t_r	Current Rise Time			41			
$t_{d(off)}$	Turn-off Delay Time			620			
t_f	Current Fall Time			110			
E_{on1}	Turn-on Switching Energy ^④				8045		μJ
E_{on2}	Turn-on Switching Energy (Diode) ^⑤				9620		
E_{off}	Turn-off Switching Energy ^⑥				7640		
$t_{d(on)}$	Turn-on Delay Time		Inductive Switching (125°C) $V_{CC} = 800V$ $V_{GE} = 15V$ $I_C = 75A$ $R_G = 1.0\Omega^{\text{⑦}}$ $T_J = +125^\circ\text{C}$		60		ns
t_r	Current Rise Time			41			
$t_{d(off)}$	Turn-off Delay Time			725			
t_f	Current Fall Time			200			
E_{on1}	Turn-on Switching Energy ^④				8620		μJ
E_{on2}	Turn-on Switching Energy (Diode) ^⑤				13000		
E_{off}	Turn-off Switching Energy ^⑥				11400		

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			.15	°C/W
$R_{\theta JC}$	Junction to Case (DIODE)			N/A	
W_T	Package Weight		5.9		gm

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② For Combi devices, I_{ces} includes both IGBT and FRED leakages
- ③ See MIL-STD-750 Method 3471.
- ④ E_{on1} is the clamped inductive turn-on energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. Tested in inductive switching test circuit shown in figure 21, but with a Silicon Carbide diode.
- ⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)
- ⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)
- ⑦ R_G is external gate resistance, not including $R_{G(int)}$ nor gate driver impedance. (MIC4452)
- ⑧ Current limited by lead temperature.

APT Reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

APT75GN120B2_L(G)

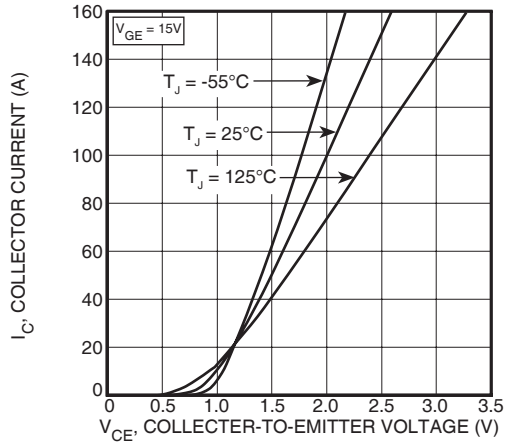


FIGURE 1, Output Characteristics ($T_J = 25^\circ\text{C}$)

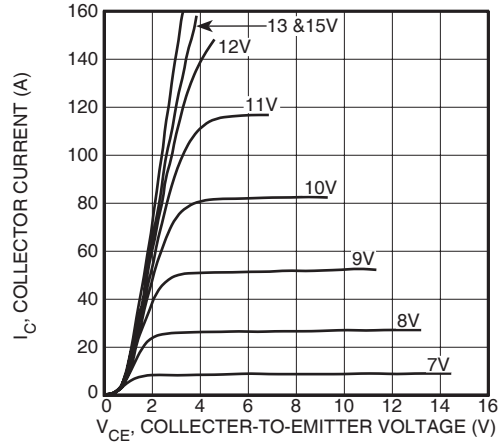


FIGURE 2, Output Characteristics ($T_J = 125^\circ\text{C}$)

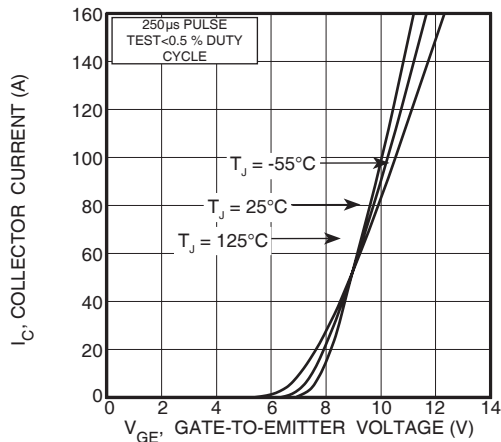


FIGURE 3, Transfer Characteristics

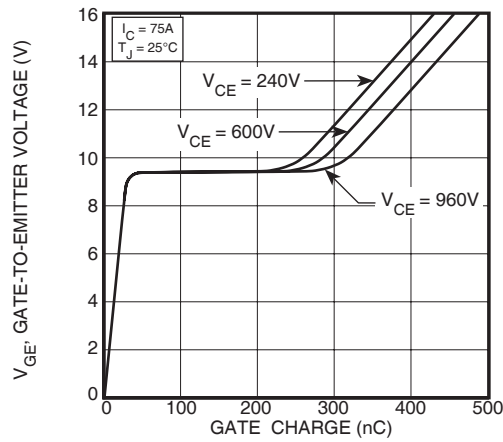


FIGURE 4, Gate Charge

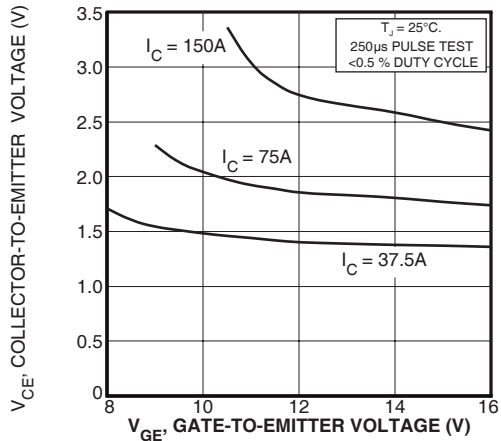


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

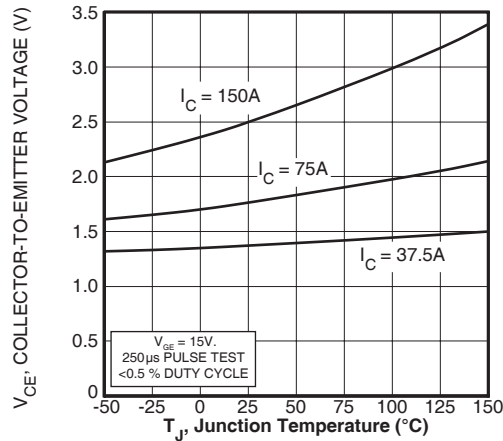


FIGURE 6, On State Voltage vs Junction Temperature

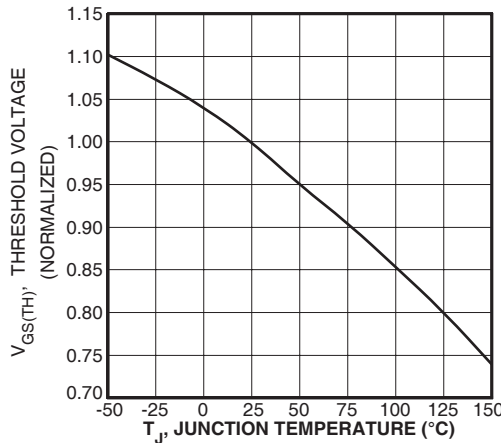


FIGURE 7, Threshold Voltage vs. Junction Temperature

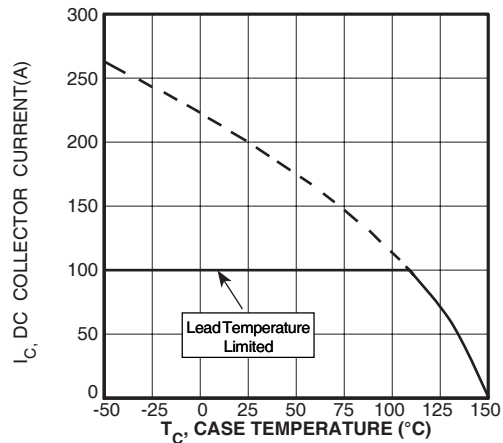


FIGURE 8, DC Collector Current vs Case Temperature

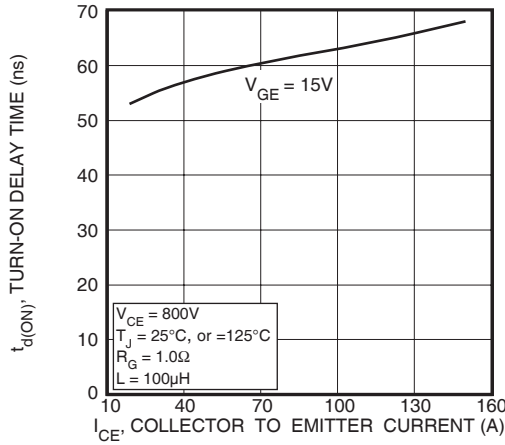


FIGURE 9, Turn-On Delay Time vs Collector Current

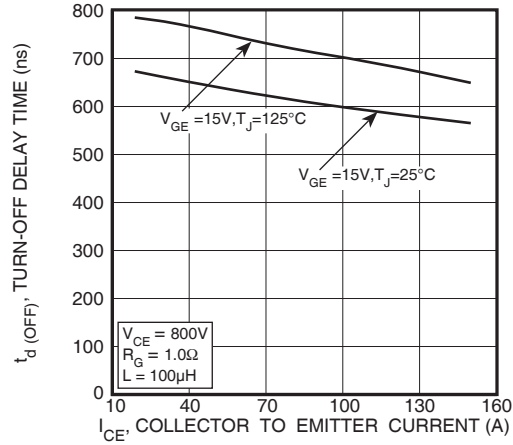


FIGURE 10, Turn-Off Delay Time vs Collector Current

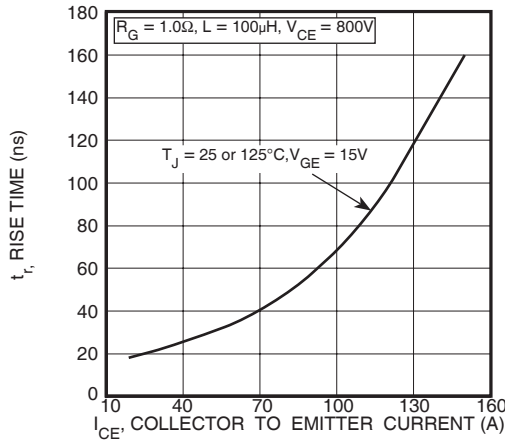


FIGURE 11, Current Rise Time vs Collector Current

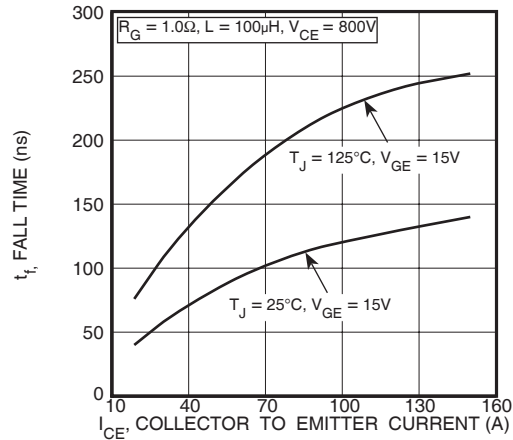


FIGURE 12, Current Fall Time vs Collector Current

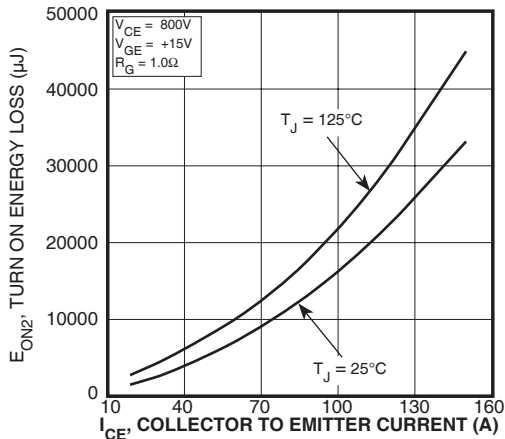


FIGURE 13, Turn-On Energy Loss vs Collector Current

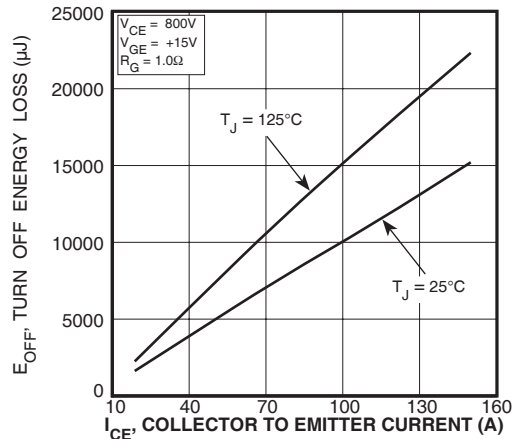


FIGURE 14, Turn Off Energy Loss vs Collector Current

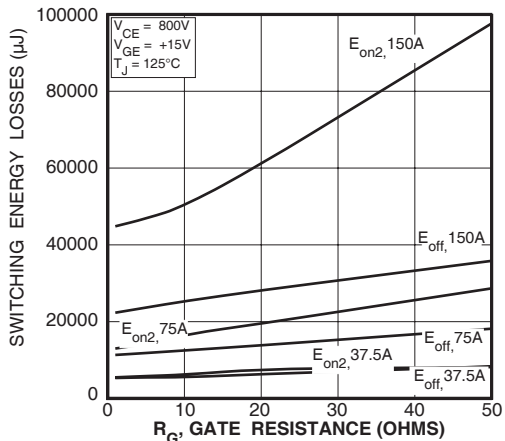


FIGURE 15, Switching Energy Losses vs. Gate Resistance

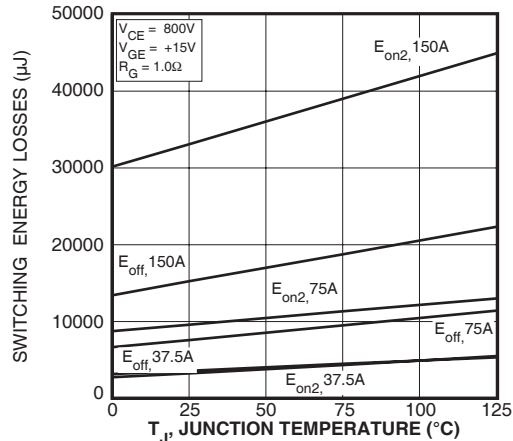


FIGURE 16, Switching Energy Losses vs Junction Temperature

TYPICAL PERFORMANCE CURVES

APT75GN120B2_L(G)

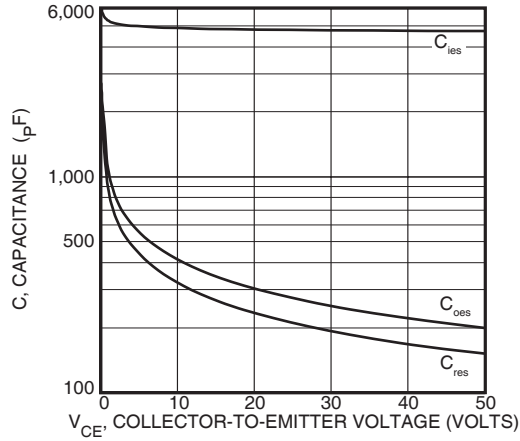


Figure 17, Capacitance vs Collector-To-Emitter Voltage

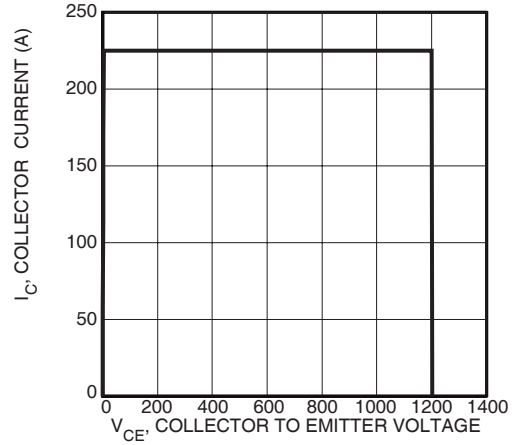


Figure 18, Minimum Switching Safe Operating Area

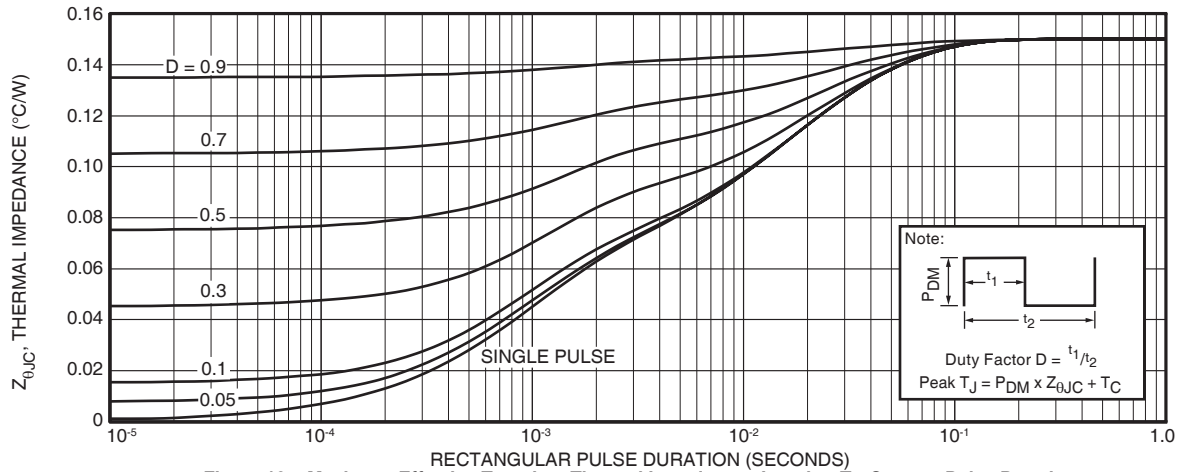


Figure 19a, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

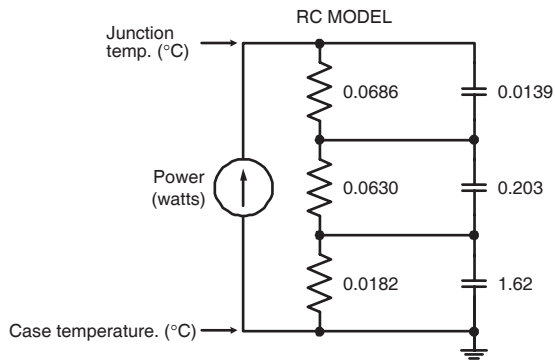


FIGURE 19b, TRANSIENT THERMAL IMPEDANCE MODEL

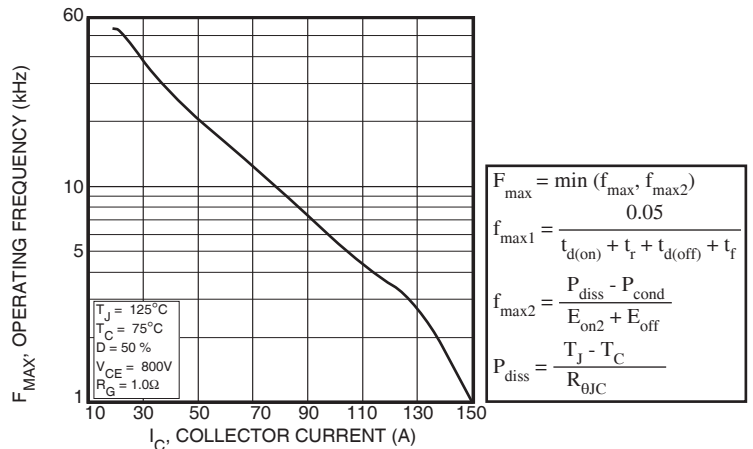


Figure 20, Operating Frequency vs Collector Current

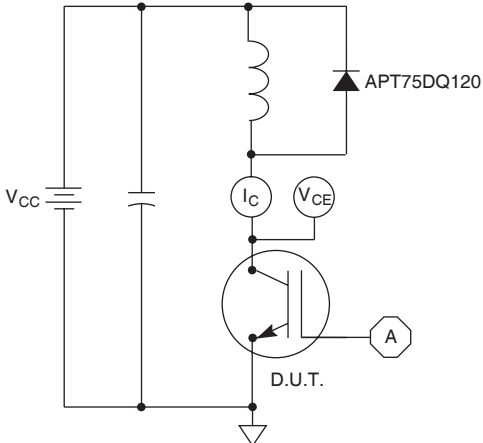


Figure 21, Inductive Switching Test Circuit

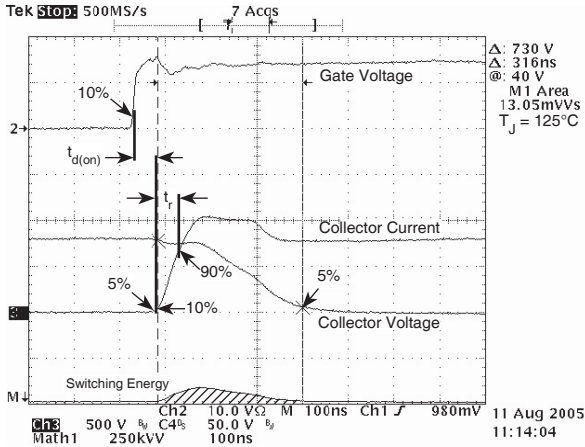


Figure 22, Turn-on Switching Waveforms and Definitions

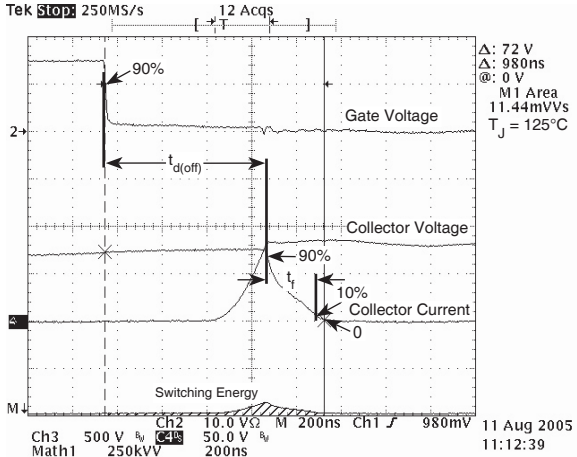
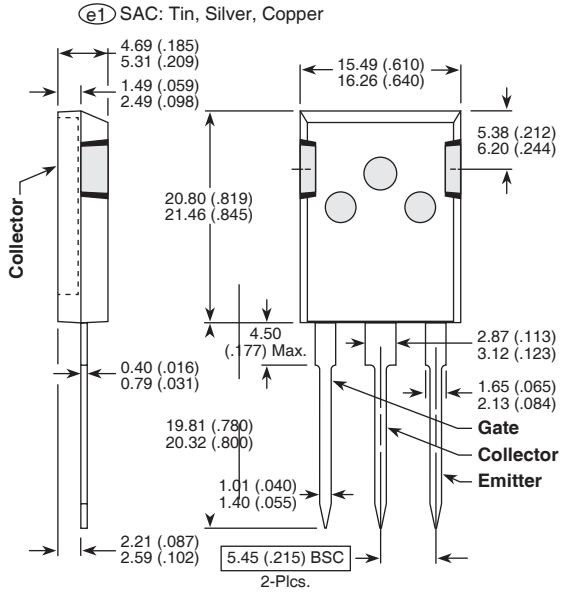


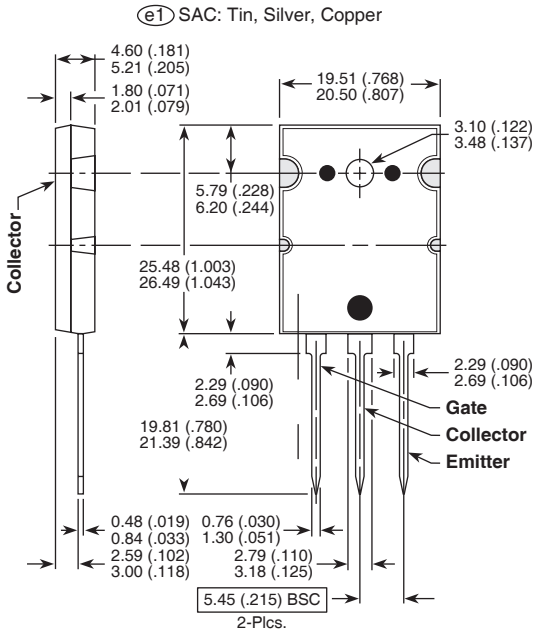
Figure 23, Turn-off Switching Waveforms and Definitions

T-MAX® (B2) Package Outline



Dimensions in Millimeters and (Inches)

TO-264(L) Package Outline



Dimensions in Millimeters and (Inches)

050-7607 Rev C 10-2005

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